

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)	PATENT APPLICATION
Inventors: Jer-Shen Maa, Jong-Jan Lee,)	
Douglas J. Tweet and)	
Sheng Teng Hsu)	
Serial No.: Not Yet Assigned)	Attorney Docket No.
Filed: Herewith)	SLA 0749
Title: METHOD OF FORMING)	
RELAXED SiGe LAYER)	

Honorable Commissioner for Patents
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to
37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by
the Examiner and made of record in the above-identified application.

(Date) 7/22/03

Respectfully submitted,

David C. Ripma
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1449A/PTO Rev. 10/95		U.S. Department of Commerce Patent and Trademark Office		Complete If Known	
				Application Number	
				Filing Date	07-22-03
				First Named Inventor	Jer-shen Maa
				Group Art Unit	
LIST OF PRIOR ART CITED BY APPLICANT (use as many sheets as necessary)				Examiner Name	
Sheet	1	of	2	Attorney Docket No.	SLA.0749

U.S. PATENT DOCUMENTS						
Examiner Initials	Cite No. ¹	U.S. Patent Document Kind Number		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YY	Pages, Columns, Lines, Where Relevant Passages or Figures Appear
			Code ² (if known)			
		6,562,703 B1		Maa et al.	05-13-03	
		6,464,780 B1		Mantl <i>et al.</i>	10-15-02	
		6,486,008 B1		Lee	11-26-02	
		5,877,070		Goesele <i>et al.</i>	03-02-99	

FOREIGN PATENT DOCUMENTS								
Examiner Initials	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YY	Pages, Columns, Lines, Where Relevant Passages or Figures Appear	T ⁶
		Office Code ³	Number ⁴	Kind				

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, country where published, source.	T ²
		G.F. CEROFOLINI et al., <i>Hydrogen-related Complexes as the Stressing Species in High-fluence, Hydrogen-implanted, Single-crystal Silicon</i> , Physical Review B, vol. 46, p. 2061 (1992)	
		DEEPAK K. NAYAK et al., <i>High-Mobility Strained-Si PMOSFETs</i> , IEEE Transactions on Electron Devices, Vol. 43, 1709 (1996)	
		ADITYA AGARWAL et al., <i>Efficient Production of Silicon-on-Insulator Films by Co-implantation of He⁺ with H⁺</i> , Proceedings of the 1997 IEEE International SOI Conference, p. 44, (1997).	

Examiner Signature		Date Considered	
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Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.1⁶ if possible. ⁶Applicant is to place a check mark here if English language Translation is attached



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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, country where published, source.	T ²
		M.K. WELDON <i>et al.</i> , <i>On the Mechanism of the Hydrogen-Induced Exfoliation of Silicon</i> , J. Vac. Sci. Technol. B. 15, 1065, (1997)	
		S. MANTL <i>et al.</i> , <i>Strain Relaxation of Epitaxial SiGe Layers on Si(100) Improved by Hydrogen Implantation</i> , Nuclear Instruments and Methods in Physics Research B 147, 29, (1999)	
		H. TRINKAUS <i>et al.</i> , <i>Strain Relaxation Mechanism for Hydrogen-Implanted Si_{1-x}Ge_x/Si(100) Heterostructures</i> , Appl. Phys. Lett., 76, 3552, (2000)	
		K. RIM <i>et al.</i> , <i>Strained Si NMOSFETs for High Performance CMOS Technology</i> , 2001 Symposium on VLSI Technology Digest of Technical Papers, p. 59, (IEEE 2001)	
		JASON T.S. LIN <i>et al.</i> , <i>Nova Cut™ Process: Fabrication of Silicon-on Insulator Materials</i> , 2002 IEEE International SOI Conference, Williamsburg, Virginia, (2002)	
		M. LUYSEBERG <i>et al.</i> , <i>Effect of helium ion implantation and annealing on the relaxation behavior of pseudomorphic Si_{1-x}Ge_x Buffer Layers on Si(100) substrates</i> , Journal of Applied Physics, Vol. 92, No. 8 (2002)	

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